

Abstract of the Disclosure

A semiconductor laser device is constructed by stacking a buffer layer, an undoped GaN layer, an n-GaN contact layer, an n-InGaN crack preventing layer, an n-AlGaN cladding layer, 5 a light emitting layer, a p-AlGaN cladding layer, and a p-GaN contact layer in this order. A ridge portion comprising the p-GaN contact layer and the p-AlGaN cladding layer is formed, and the thickness of the p-AlGaN cladding layer in the ridge portion is less than 0.3 μm .